



SANYO Semiconductors

DATA SHEET

2SB892 / 2SD1207 — PNP / NPN Epitaxial Planar Silicon Transistors Large-Current Switching Applications

Applications

- Power supplies, relay drivers, lamp drivers, and automotive wiring.

Features

- FBET and MBIT processed (Original process of SANYO).
- Low saturation voltage.
- Large current capacity and wide ASO.

Specifications () : 2SB892

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)60	V
Collector-to-Emitter Voltage	VCEO		(-)50	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)2	A
Collector Current (Pulse)	ICP		(-)4	A
Collector Dissipation	PC		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	VCB=(-)50V, IE=0A			(-)0.1	μA
Emitter Cutoff Current	IEBO	VEB=(-)4V, IC=0A			(-)0.1	μA

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2SB892 / 2SD1207

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
DC Current Gain	h_{FE1}^*	$V_{CE}=(-)2V, I_C=(-)100mA$	100		560	
	h_{FE2}	$V_{CE}=(-)2V, I_C=(-)1.5A$	40			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)50mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		(22)12		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-0.3)0.15	(-0.7)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-)0.9	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0A$	(-)6			V

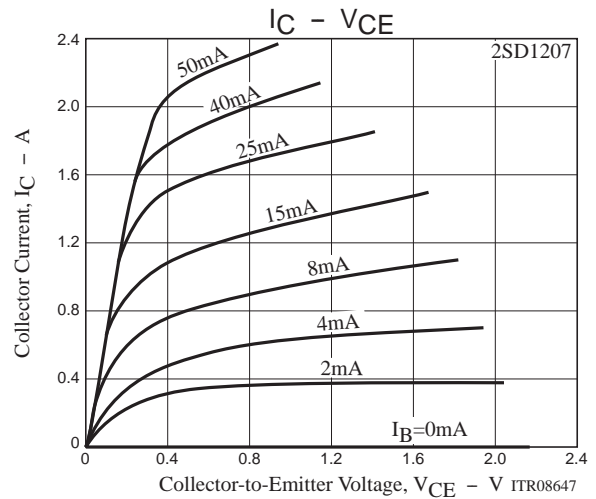
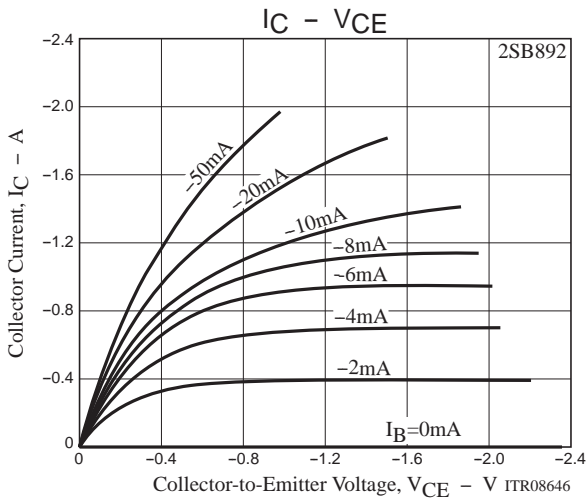
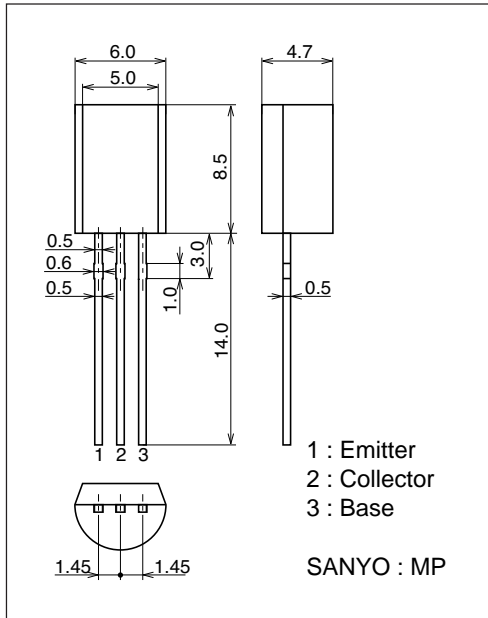
* : The 2SB892 / 2SD1207 are graded as follows by h_{FE} at 100mA :

Rank	R	S	T	U
h_{FE}	100 to 200	140 to 280	200 to 400	280 to 560

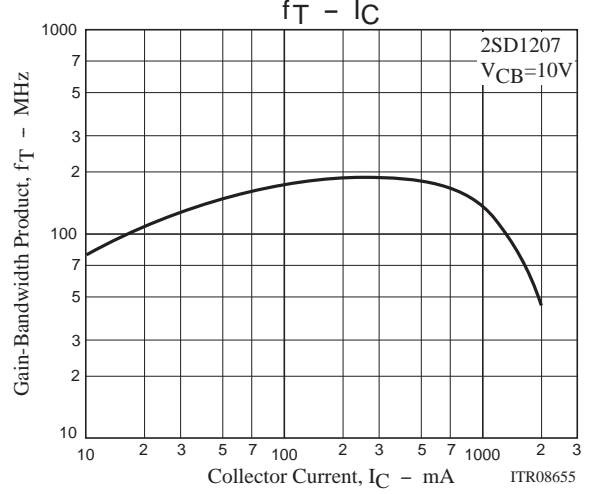
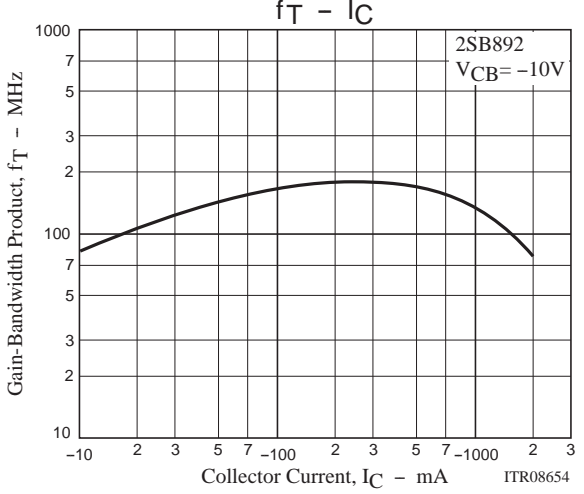
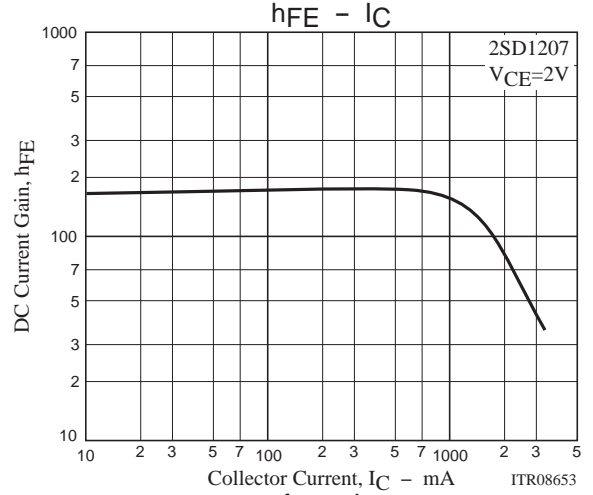
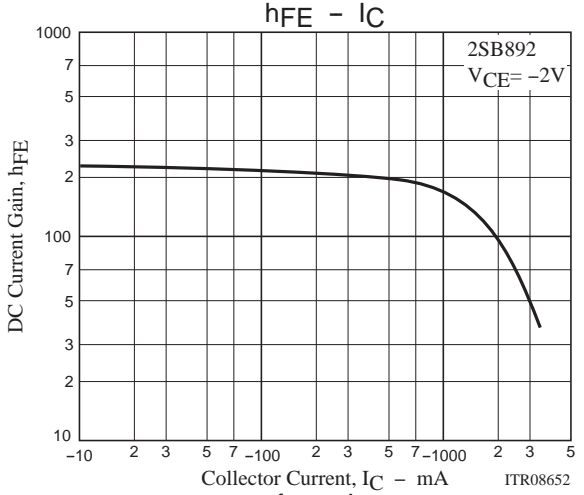
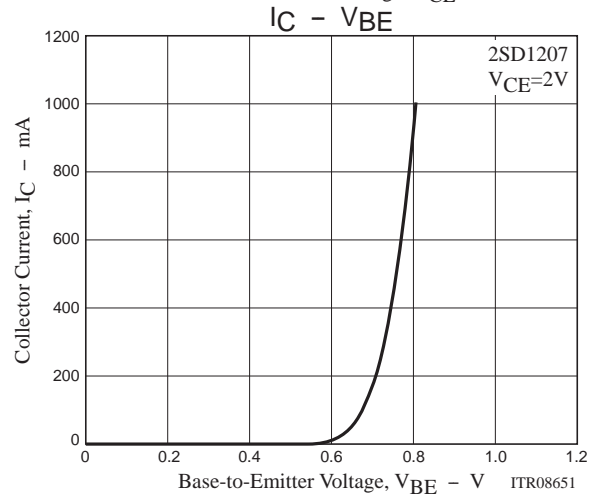
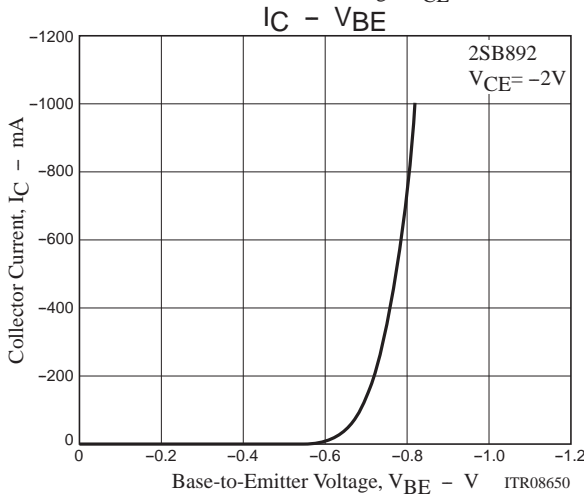
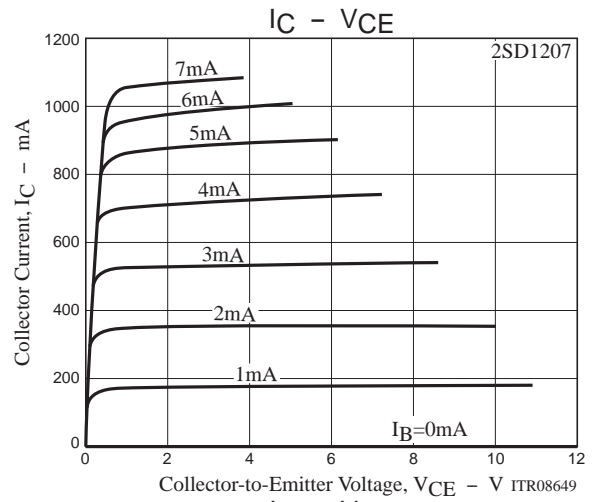
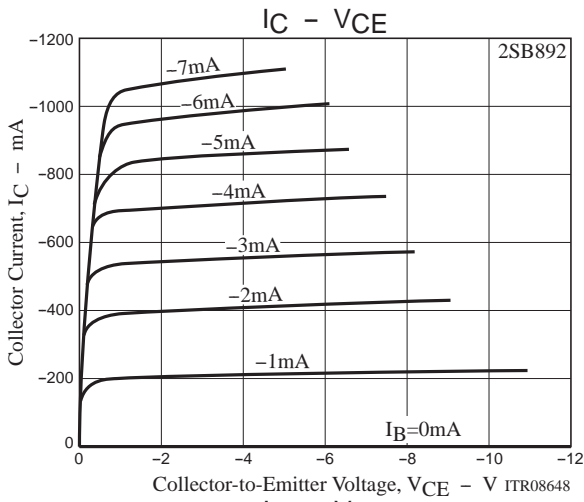
Package Dimensions

unit : mm (typ)

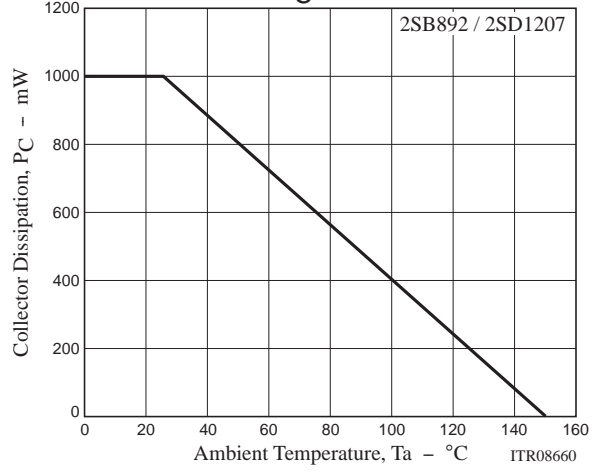
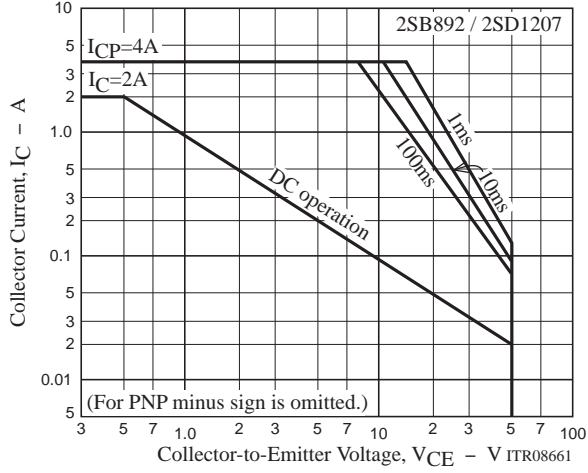
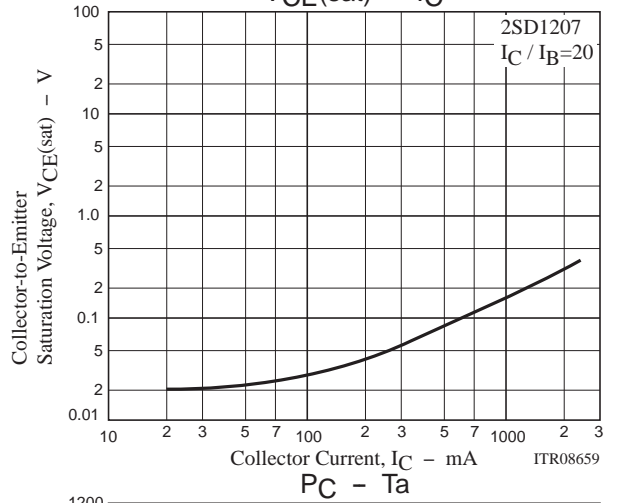
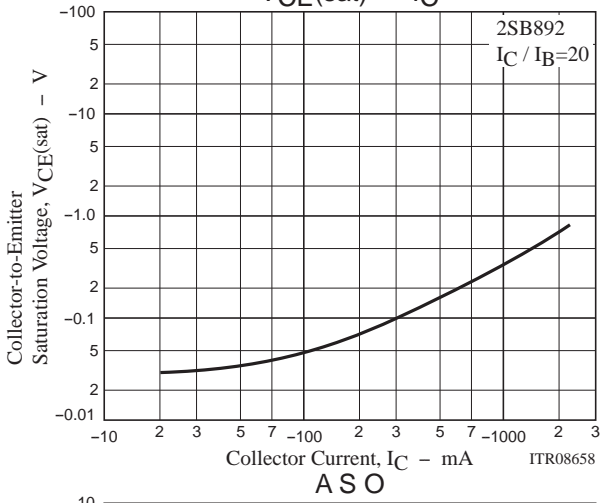
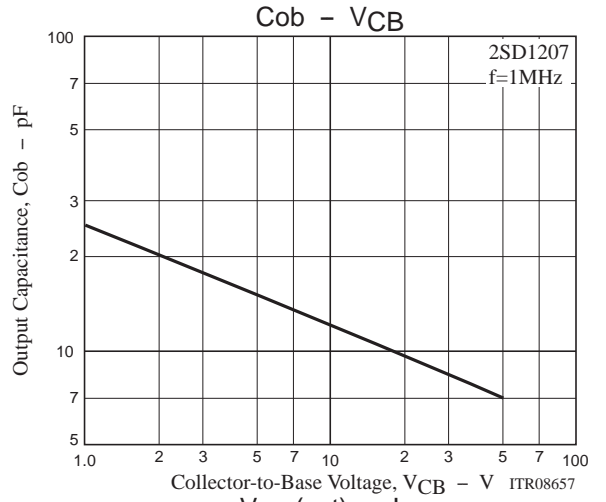
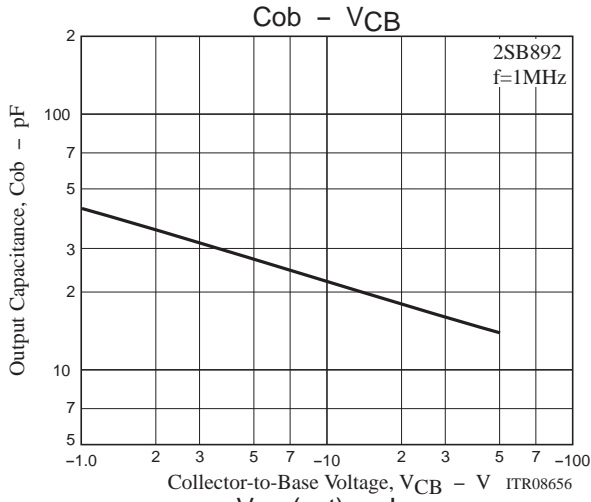
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2SB892 / 2SD1207



2SB892 / 2SD1207



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